

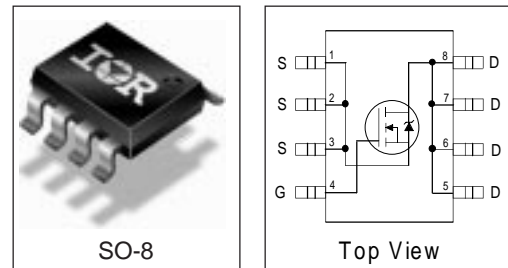
- N-Channel Application-Specific MOSFETs
- Ideal for CPU Core DC-DC Converters
- Low Conduction Losses
- Low Switching Losses
- Minimizes Parallel MOSFETs for high current applications

Description

This new device employs advanced HEXFET Power MOSFET technology to achieve an unprecedented balance of on-resistance and gate charge. The reduced conduction and switching losses make it ideal for high efficiency DC-DC converters that power the latest generation of microprocessors.

The IRF7811AV has been optimized for all parameters that are critical in synchronous buck converters including $R_{DS(on)}$, gate charge and Cdv/dt -induced turn-on immunity. The IRF7811AV offers an extremely low combination of Q_{sw} & $R_{DS(on)}$ for reduced losses in both control and synchronous FET applications.

The package is designed for vapor phase, infra-red, convection, or wave soldering techniques. Power dissipation of greater than 2W is possible in a typical PCB mount application.



DEVICE CHARACTERISTICS ⑤

IRF7811AV	
$R_{DS(on)}$	11mΩ
Q_G	17nC
Q_{sw}	6.7nC
Q_{oss}	8.1nC

Absolute Maximum Ratings

Parameter	Symbol	IRF7811AV	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	
Continuous Drain or Source Current ($V_{GS} \geq 4.5V$)	$T_A = 25^\circ C$	10.8	A
	$T_L = 90^\circ C$	11.8	
Pulsed Drain Current①	I_{DM}	100	
Power Dissipation③	$T_A = 25^\circ C$	2.5	W
	$T_L = 90^\circ C$	3.0	
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C
Continuous Source Current (Body Diode)	I_S	2.5	A
Pulsed Source Current①	I_{SM}	50	

Thermal Resistance

Parameter		Max.	Units
Maximum Junction-to-Ambient③	$R_{\theta JA}$	50	°C/W
Maximum Junction-to-Lead	$R_{\theta JL}$	20	°C/W

Electrical Characteristics

Parameter		Min	Typ	Max	Units	Conditions
Drain-to-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Static Drain-Source on Resistance	$R_{DS(on)}$		11	14	$m\Omega$	$V_{GS} = 4.5V, I_D = 15A$ ②
Gate Threshold Voltage	$V_{GS(th)}$	1.0			V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Drain-Source Leakage Current	I_{DSS}			20	μA	$V_{DS} = 24V, V_{GS} = 0$
				100		$V_{DS} = 24V, V_{GS} = 0,$ $T_j = 100^\circ C$
Gate-Source Leakage Current	I_{GSS}			± 100	nA	$V_{GS} = \pm 20V$
Total Gate Chg Cont FET	Q_G		17	26	nC	$V_{GS} = 5V, I_D = 15A, V_{DS} = 24V$
Total Gate Chg Sync FET	Q_G		14	21		$V_{GS} = 5V, V_{DS} < 100mV$
Pre-Vth Gate-Source Charge	Q_{GS1}		3.4			$V_{DS} = 16V, I_D = 15A$
Post-Vth Gate-Source Charge	Q_{GS2}		1.6			
Gate to Drain Charge	Q_{GD}		5.1			
Switch Chg($Q_{gs2} + Q_{gd}$)	Q_{sw}		6.7			
Output Charge	Q_{oss}		8.1	12		$V_{DS} = 16V, V_{GS} = 0$
Gate Resistance	R_G		2.2		Ω	
Turn-on Delay Time	$t_{d(on)}$		8.6		ns	$V_{DD} = 16V, I_D = 15A$ $V_{GS} = 5V$ Clamped Inductive Load
Rise Time	t_r		21			
Turn-off Delay Time	$t_{d(off)}$		43			
Fall Time	t_f		10			
Input Capacitance	C_{iss}	-	1801	-	pF	$V_{DS} = 16V, V_{GS} = 0$
Output Capacitance	C_{oss}	-	723	-		
Reverse Transfer Capacitance	C_{rss}	-	46	-		

Source-Drain Rating & Characteristics

Parameter		Min	Typ	Max	Units	Conditions
Diode Forward Voltage	V_{SD}			1.3	V	$I_S = 15A$ ②, $V_{GS} = 0V$
Reverse Recovery Charge④	Q_{rr}		50		nC	$di/dt \sim 700A/\mu s$ $V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$
Reverse Recovery Charge (with Parallel Schottky)⑤	$Q_{rr(s)}$		43		nC	$di/dt = 700A/\mu s$ (with 10BQ040) $V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400 \mu s$; duty cycle $\leq 2\%$.
- ③ When mounted on 1 inch square copper board, $t < 10$ sec.
- ④ Typ = measured - Q_{oss}
- ⑤ Typical values of $R_{DS(on)}$ measured at $V_{GS} = 4.5V$, Q_G , Q_{sw} and Q_{oss} measured at $V_{GS} = 5.0V, I_F = 15A$.

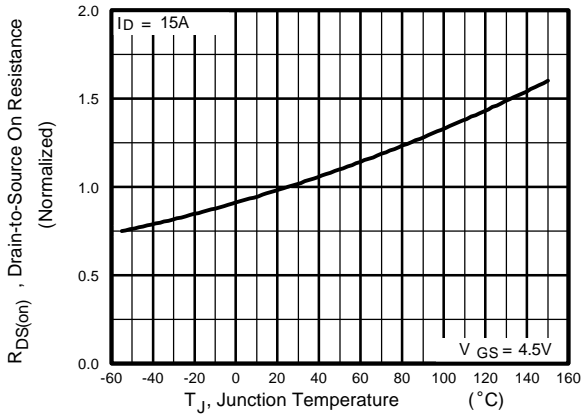


Figure 1. Normalized On-Resistance vs. Temperature

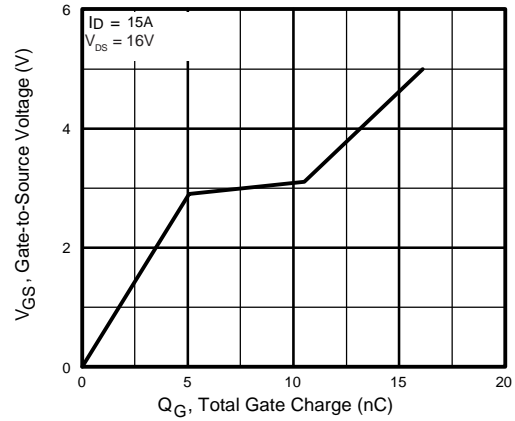


Figure 2. Gate-to-Source Voltage vs. Typical Gate Charge

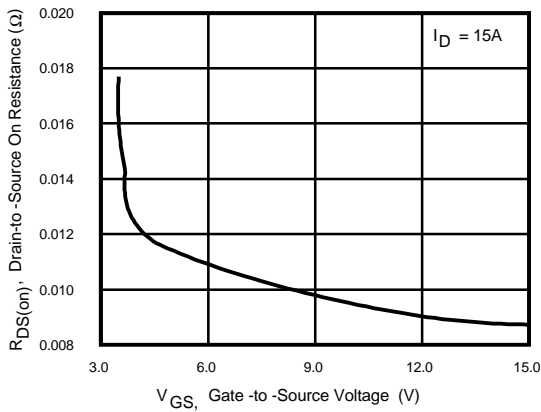


Figure 3. Typical $R_{DS(on)}$ vs. Gate-to-Source Voltage

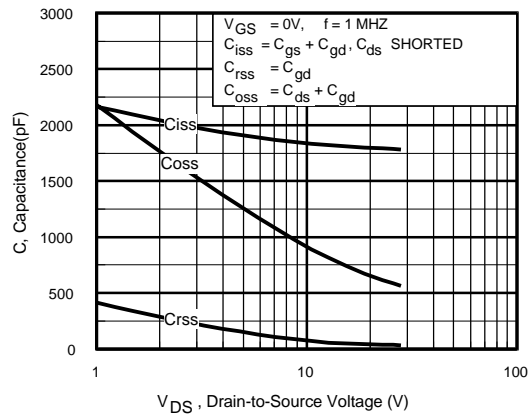


Figure 4. Typical Capacitance vs. Drain-to-Source Voltage

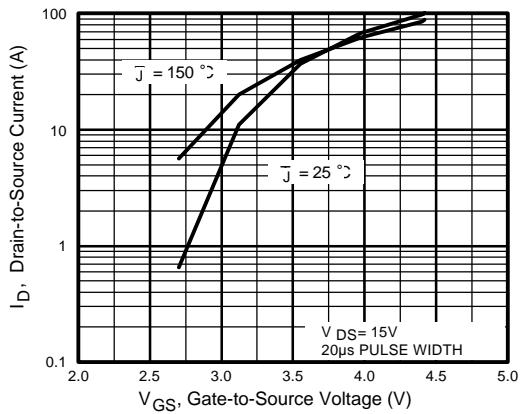


Figure 5. Typical Transfer Characteristics

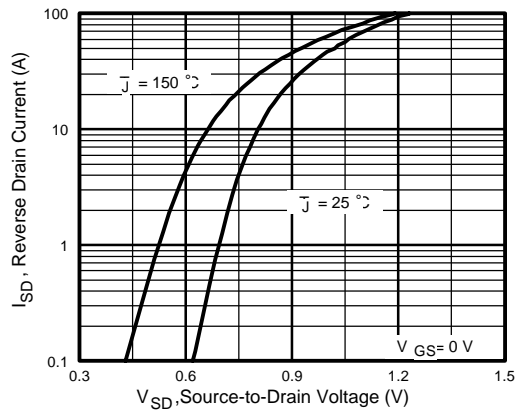


Figure 6. Typical Source-Drain Diode Forward Voltage

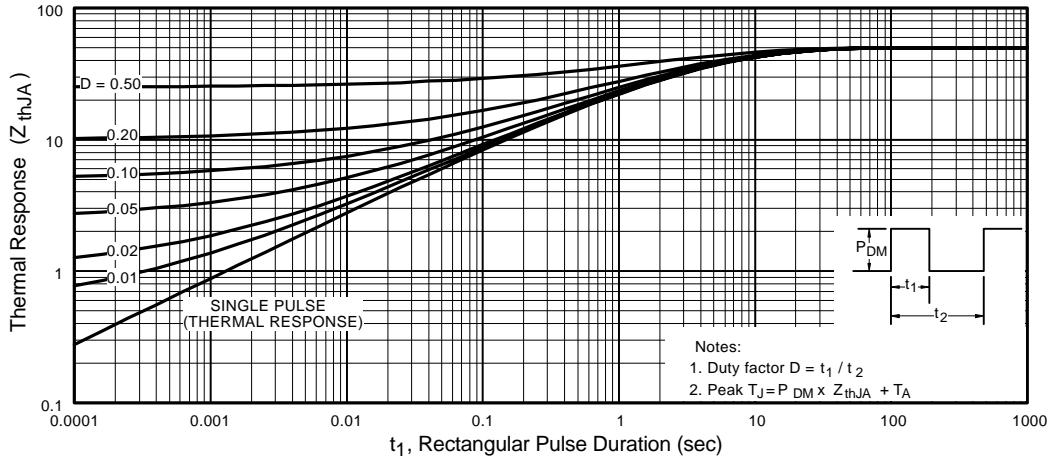


Figure 7. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

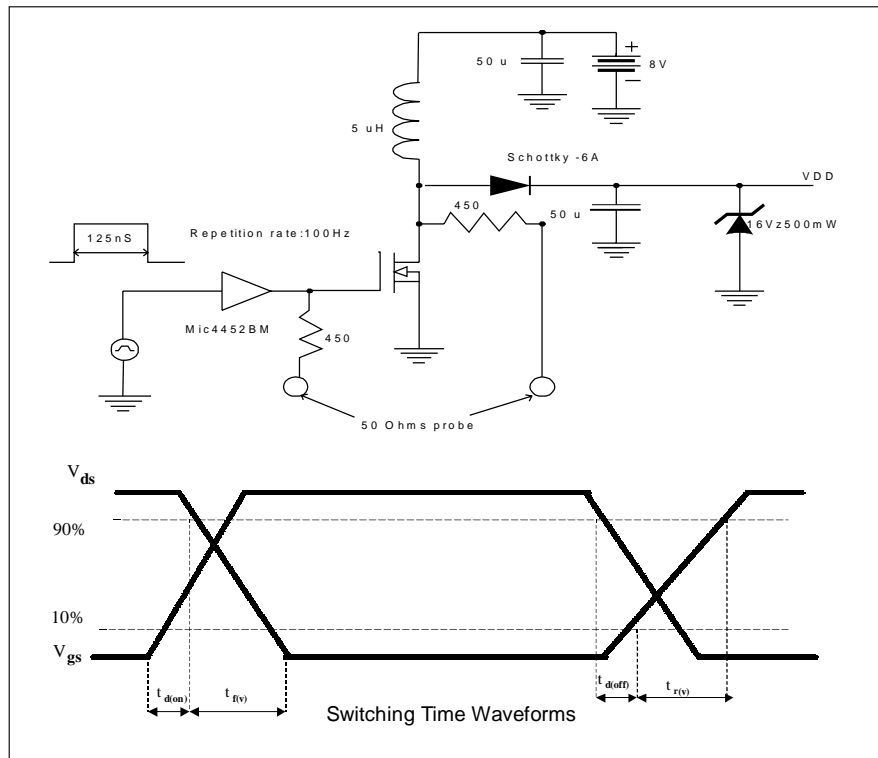
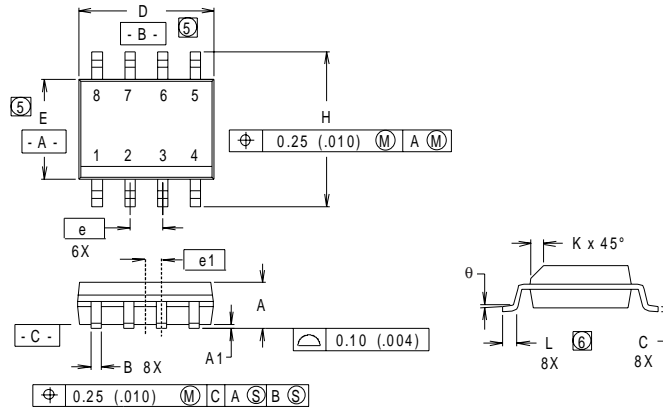


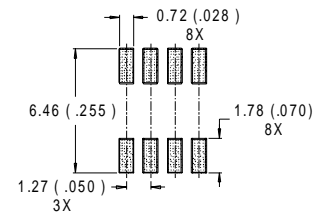
Figure 8. Clamped Inductive load test diagram and switching waveform

SO-8 Package Details



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
θ	0°	8°	0°	8°

RECOMMENDED FOOTPRINT

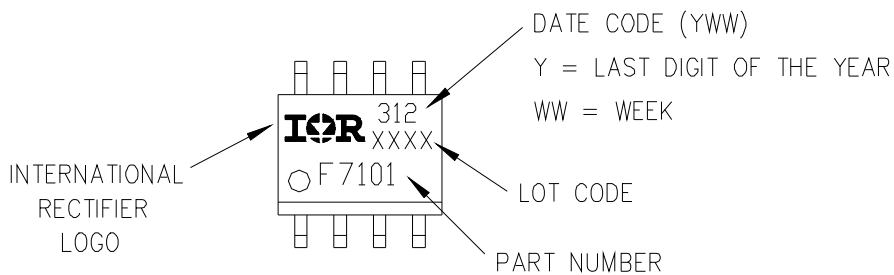


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANS Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
6. DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

SO-8 Part Marking

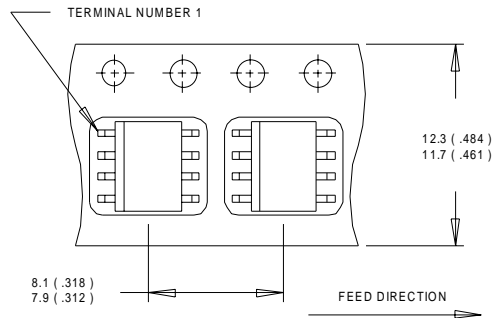
EXAMPLE: THIS IS AN IRF7101



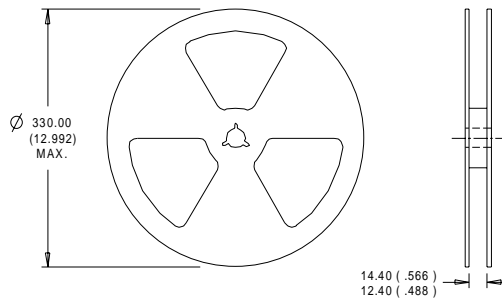
IRF7811AV

International
IR Rectifier

SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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